Type-II Quantum Dot Nanowire Structures with Large Oscillator Strengths for Optical Quantum Gating Applications

The exciton oscillator strength (OS) in type-II quantum dot (QD) nanowires is calculated by using a fast and efficient method. We propose a new structure in Double-Well QD (DWQD) nanowire that considerably increases OS of type-II QDs which is a key parameter in optical quantum gating in the stimulated Raman adiabatic passage (STIRAP) process [1] for implementing quantum gates.

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